

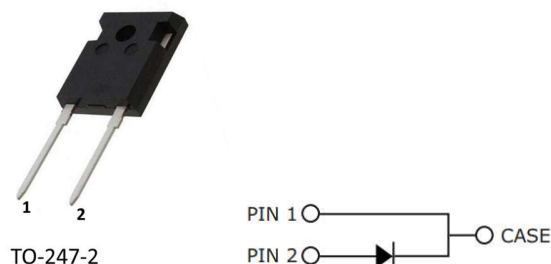
## NWK710TJ1-2

### 1700V Silicon Carbide Schottky Diode

| Parameter                           | Value | Unit |
|-------------------------------------|-------|------|
| $V_{RRM}$                           | 1700  | V    |
| $Q_C$                               | 116   | nC   |
| $I_F$ ( $T_C = 160^\circ\text{C}$ ) | 10    | A    |

### Features

- 1700 V Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Excellent Surge Current Capability
- Positive Temperature Coefficient on  $V_F$
- Temperature-Independent Switching
- High Frequency Operation



### Applications

- Switch Mode Power Supplies
- Uninterruptible Power Supplies
- Power Factor Correction
- Motor Drivers

### Description

The NWK710TJ1-2 is a 1700V, SiC Schottky Barrier Diode (SBD) based on NovaWave's advanced SiC power technology resulting in high performance and long-term reliability. It supports high-temperature operation while showing minimal losses, zero reverse recovery, and low leakage current.

### Part Description

| Part Number | Package  | Marking     |
|-------------|----------|-------------|
| NWK710TJ1-2 | TO-247-2 | NWK710TJ1-2 |

## Absolute Maximum Ratings

$T_J = 25\text{ }^{\circ}\text{C}$  except as noted. Exceeding the maximum ratings may damage the device.

| Parameter                            | Symbol        | Value       | Unit                 | Test conditions                                                            |
|--------------------------------------|---------------|-------------|----------------------|----------------------------------------------------------------------------|
| Repetitive Peak Reverse Voltage      | $V_{RRM}$     | 1700        | V                    |                                                                            |
| Continuous Forward Current           | $I_F$         | 43<br>10    | A                    | $T_C = 25\text{ }^{\circ}\text{C}$<br>$T_C = 160\text{ }^{\circ}\text{C}$  |
| Non-Repetitive Forward Surge Current | $I_{FSM}$     | 145         | A                    | $T_C = 25\text{ }^{\circ}\text{C}$ , $t_p = 10\text{ ms}$ , Half Sine Wave |
| $i^2t$ value                         | $\int i^2 dt$ | 105         | $\text{A}^2\text{s}$ | $T_C = 25\text{ }^{\circ}\text{C}$ , $t_p = 10\text{ ms}$                  |
| Power Dissipation                    | $P_{tot}$     | 294<br>127  | W                    | $T_C = 25\text{ }^{\circ}\text{C}$<br>$T_C = 110\text{ }^{\circ}\text{C}$  |
| Operating Junction Range             | $T_J$         | -55 to +175 | $^{\circ}\text{C}$   | -                                                                          |
| Storage Temperature Range            | $T_{stg}$     | -55 to +175 | $^{\circ}\text{C}$   | -                                                                          |

## Thermal Characteristics

| Parameter                                | Symbol       | Min. | Typ. | Max. | Unit                 |
|------------------------------------------|--------------|------|------|------|----------------------|
| Thermal Resistance from Junction to Case | $R_{TH,J-C}$ |      | 0.51 |      | $^{\circ}\text{C/W}$ |

## Electrical Characteristics

| Parameters                | Symbol   | Min  | Typ                  | Max                  | Unit          | Condition                                                                                                                                                                                                                             |
|---------------------------|----------|------|----------------------|----------------------|---------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| DC blocking voltage       | $V_{DC}$ | 1700 | --                   | --                   | V             | $T_C = 25\text{ }^{\circ}\text{C}$                                                                                                                                                                                                    |
| Forward Voltage           | $V_F$    | --   | 1.38<br>1.75<br>1.98 | 1.60<br>2.35<br>2.72 | V             | $I_F=10\text{ A}$ , $T_C = 25\text{ }^{\circ}\text{C}$<br>$I_F=10\text{ A}$ , $T_C = 135\text{ }^{\circ}\text{C}$<br>$I_F=10\text{ A}$ , $T_C = 175\text{ }^{\circ}\text{C}$                                                          |
| Reverse Current           | $I_R$    | --   | 0.5<br>6             | 200<br>400           | $\mu\text{A}$ | $V_R=1700\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$<br>$V_R=1700\text{ V}$ , $T_C = 175\text{ }^{\circ}\text{C}$                                                                                                                 |
| Total Capacitive Charge   | $Q_C$    | --   | 116                  | --                   | nC            | $V_R=1700\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$ ,<br>$Q_C=\int_0^{V_R} C(V)dV$                                                                                                                                               |
| Total Capacitance         | $C$      | --   | 662<br>53<br>43      | --                   | pF            | $V_R=1\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$ , $f=1\text{ MHz}$<br>$V_R=800\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$ , $f=1\text{ MHz}$<br>$V_R=1700\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$ , $f=1\text{ MHz}$ |
| Capacitance Stored Energy | $E_C$    | --   | 72                   | --                   | $\mu\text{J}$ | $V_R=1700\text{ V}$ , $T_C = 25\text{ }^{\circ}\text{C}$                                                                                                                                                                              |

## Electrical Performance Graphs

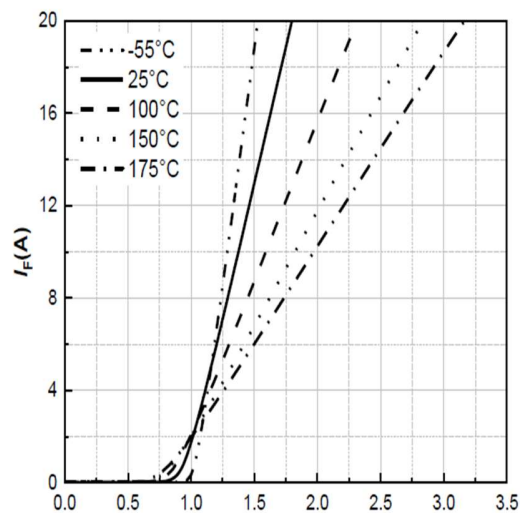


Figure 1: Typical Forward Characteristics

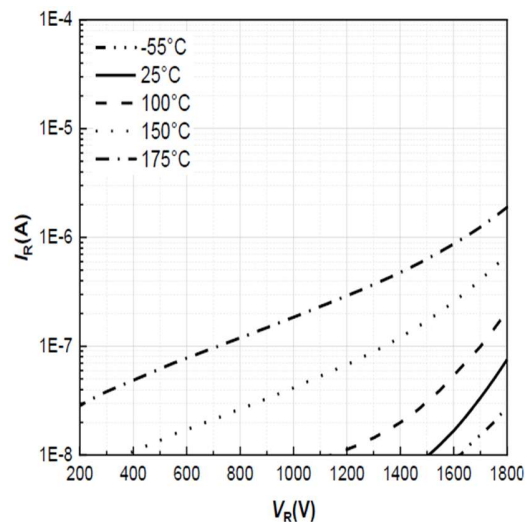


Figure 2: Typical reverse current as function of reverse voltage

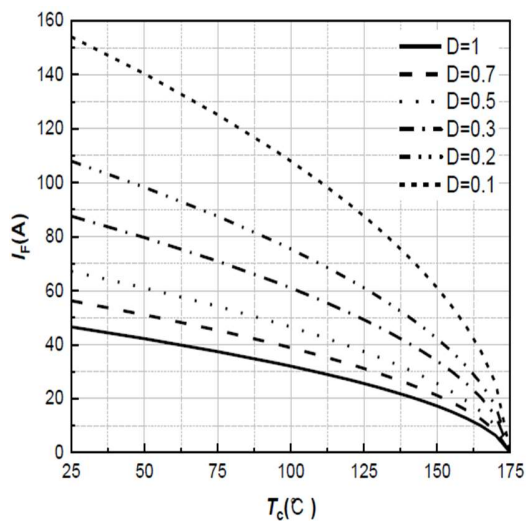


Figure 3: Diode forward current as function of temperature, D=duty cycle

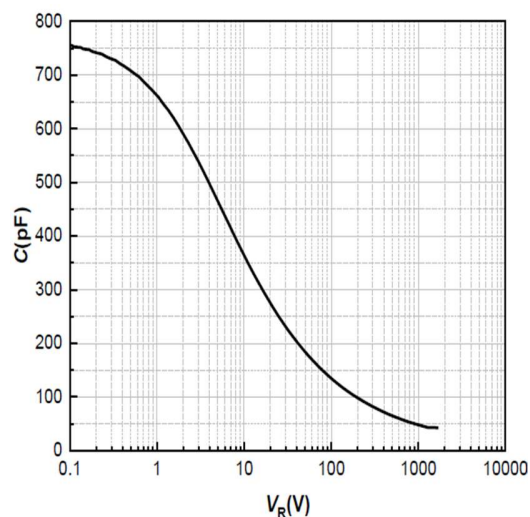


Figure 4: Typical capacitance as function of reverse voltage,  $C=f(V_R)$ ;  
 $T_J=25^\circ\text{C}$ ;  $f=1\text{ MHz}$

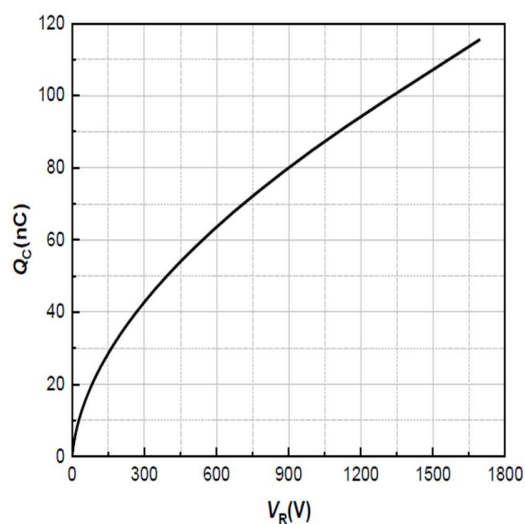


Figure 5: Typical reverse charge as function of reverse voltage

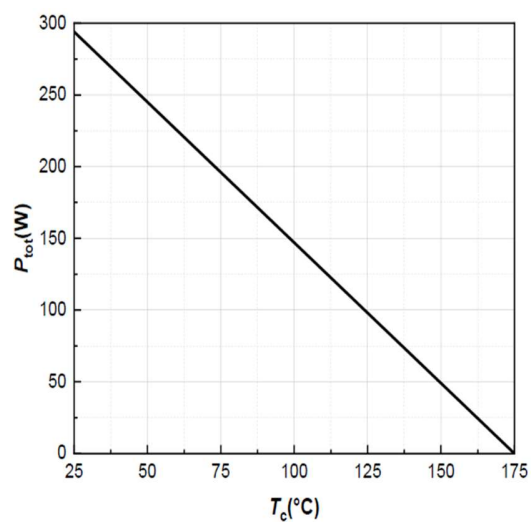


Figure 6: Power dissipation as function of case temperature

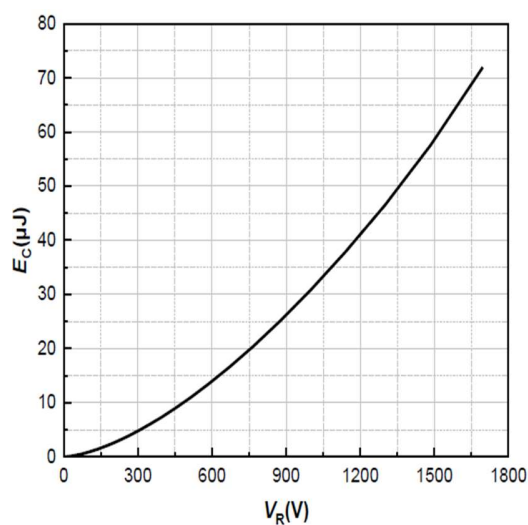


Figure 7: Typical Capacitance Stored Energy

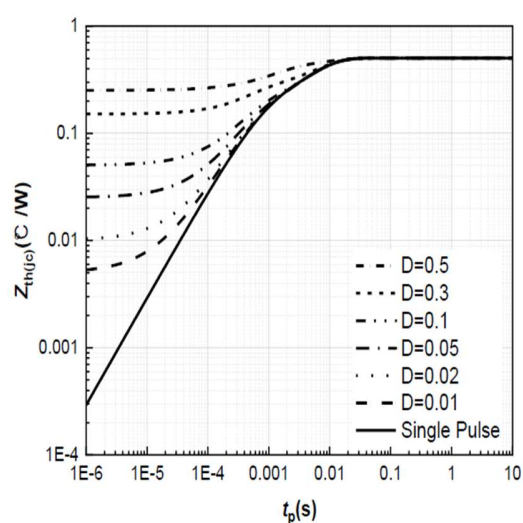
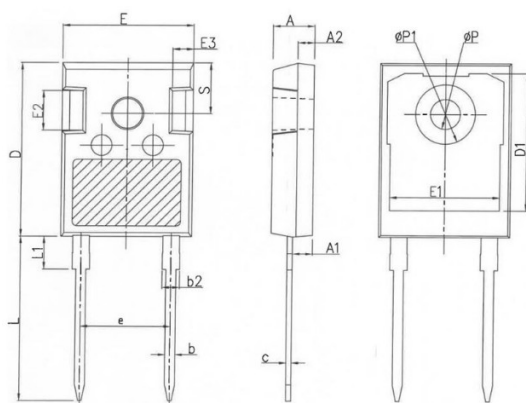


Figure 8: Max. transient thermal impedance,  $Z_{th(jc)} = f(t_p)$ , parameter:  $D = t_p/T$

## Package Dimensions

Package: TO-247-2



| SYMBOL    | Unit:mm   |       |       |
|-----------|-----------|-------|-------|
|           | MIN       | NOM   | MAX   |
| A         | 4.80      | 5.00  | 5.20  |
| A1        | 2.21      | 2.41  | 2.59  |
| A2        | 1.85      | 2.00  | 2.15  |
| b         | 1.11      | 1.21  | 1.36  |
| b2        | 1.91      | 2.01  | 2.21  |
| c         | 0.51      | 0.61  | 0.75  |
| D         | 20.70     | 21.00 | 21.30 |
| D1        | 16.25     | 16.55 | 16.85 |
| E         | 15.50     | 15.80 | 16.10 |
| E1        | 13.00     | 13.30 | 13.60 |
| E2        | 4.80      | 5.00  | 5.20  |
| E3        | 2.30      | 2.50  | 2.70  |
| e         | 10.88 BSC |       |       |
| L         | 19.62     | 19.92 | 20.22 |
| L1        | -         | -     | 4.30  |
| $\phi P$  | 3.40      | 3.60  | 3.80  |
| $\phi P1$ | -         | -     | 7.30  |
| S         | 6.15 BSC  |       |       |



## Disclaimer

The information given in this document is intended as a reference only and shall not in any event be regarded as a guarantee of performance. Novawave does not assume any liability arising out of the use of any product described herein, including but not limited to any personal injury, death, or property or environmental damage. The products shown herein are not designed for use as critical components in medical, life-saving, or life-sustaining applications, whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness. No licenses, patent rights, or any other intellectual property rights is granted or conveyed. Novawave reserves the right to make changes without further notice to any products herein to improve reliability, function, or design. Novawave standard terms and conditions apply. All rights reserved.